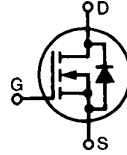


# MegaMOS™ FET

## IXTH 14N80

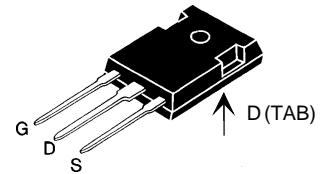
$V_{DSS} = 800\text{ V}$   
 $I_{D25} = 14\text{ A}$   
 $R_{DS(on)} = 0.70\ \Omega$

### N-Channel Enhancement Mode



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	800	V
$V_{DGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1\text{ M}\Omega$	800	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	14	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	56	A
$P_D$	$T_C = 25^\circ\text{C}$	300	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
Max. lead temperature for soldering		300	$^\circ\text{C}$
1.6 mm (0.063 in) from case for 10 s			
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		6	g

### TO-247 AD



G = Gate,      D = Drain,  
 S = Source,    TAB = Drain

### Features

- International standard package
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Low package inductance (< 5 nH)
  - easy to drive and to protect
- Fast switching times

### Applications

- Switch-mode and resonant-mode power supplies
- Motor control
- Uninterruptible Power Supplies (UPS)
- DC choppers

### Advantages

- Easy to mount with 1 screw (isolated mounting screw hole)
- Space savings
- High power density

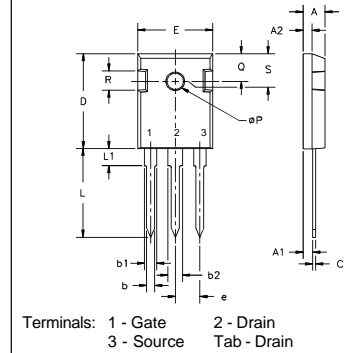
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0\text{ V}, I_D = 3\text{ mA}$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20\text{ V}_{DC}, V_{DS} = 0$			$\pm 100\text{ nA}$
$I_{DSS}$	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0\text{ V}$			250 $\mu\text{A}$ 1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			0.7 $\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ , pulse test	8	14	S	
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4500	pF	
$C_{oss}$			310	pF	
$C_{rss}$			65	pF	
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$ , (External)		20	50	ns
$t_r$			33	50	ns
$t_{d(off)}$			63	100	ns
$t_f$			32	50	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		145	170	nC
$Q_{gs}$			30	45	nC
$Q_{gd}$			55	80	nC
$R_{thJC}$			0.42	K/W	
$R_{thCK}$		0.25		K/W	

### Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			14 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			56 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$	800		ns

### TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

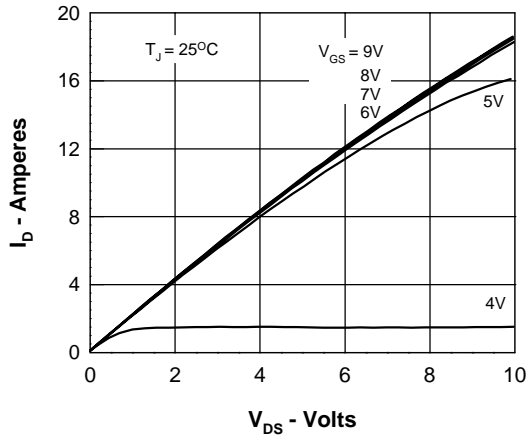
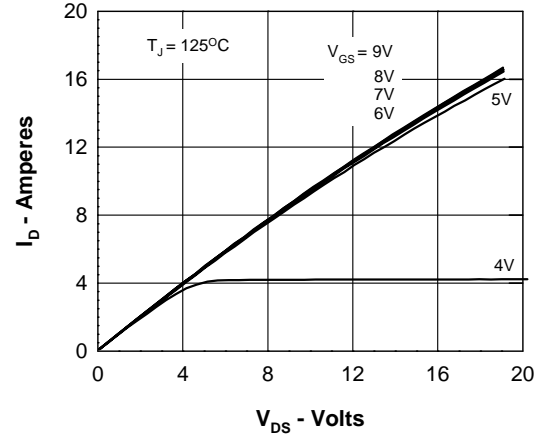
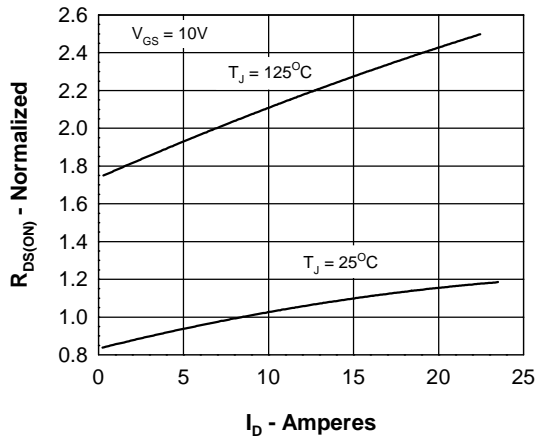
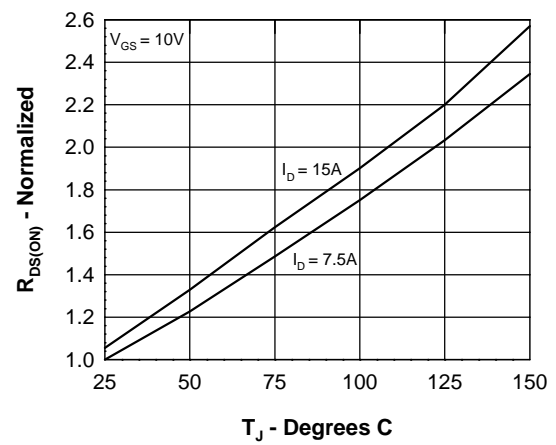
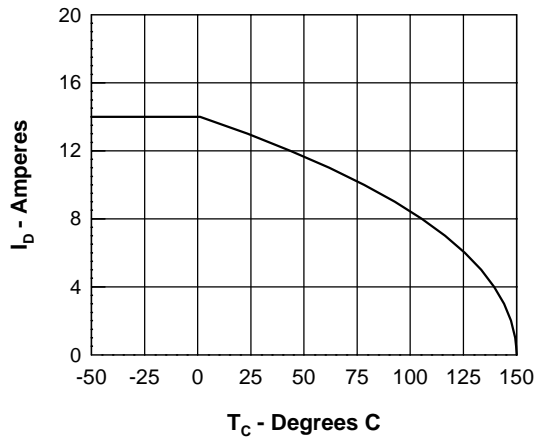
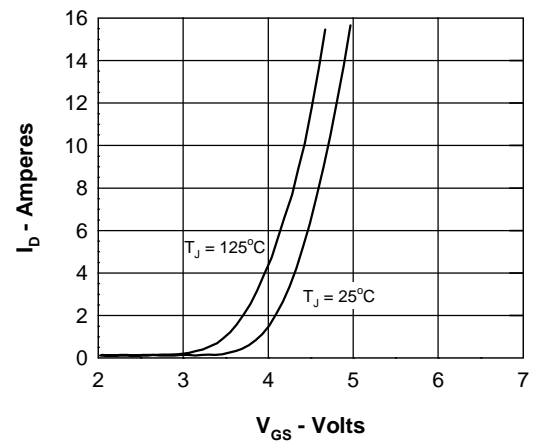
**Figure 1. Output Characteristics at 25°C**

**Figure 2. Output Characteristics at 125°C**

**Figure 3.  $R_{DS(on)}$  normalized to 0.5  $I_{D25}$  value vs.  $I_D$** 

**Figure 4.  $R_{DS(on)}$  normalized to 0.5  $I_{D25}$  value vs.  $T_J$** 

**Figure 5. Drain Current vs. Case Temperature**

**Figure 6. Admittance Curves**


Figure 7. Gate Charge

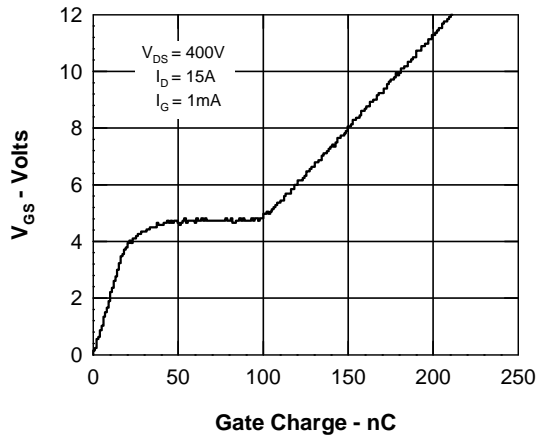


Figure 8. Capacitance Curves

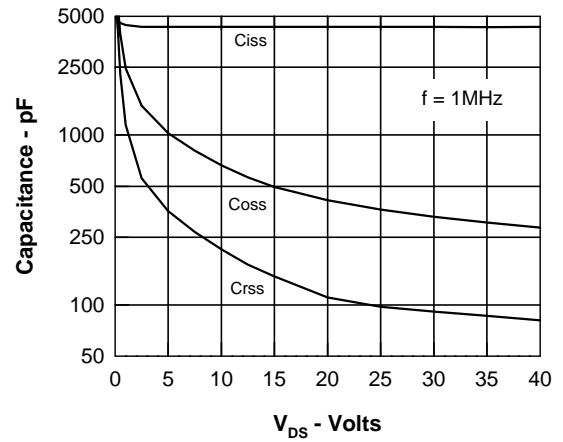


Figure 9. Source Current vs. Source to Drain Voltage

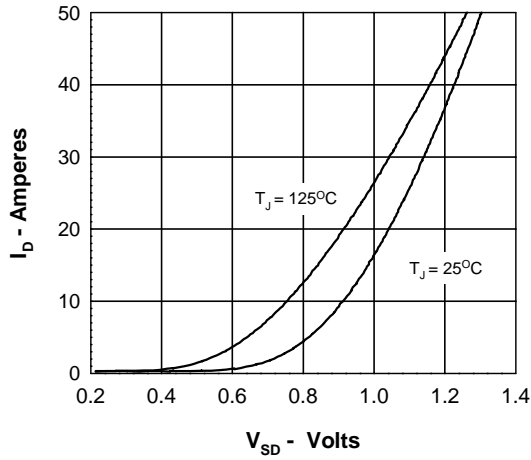


Figure 10. Forward Bias Safe Operating Area

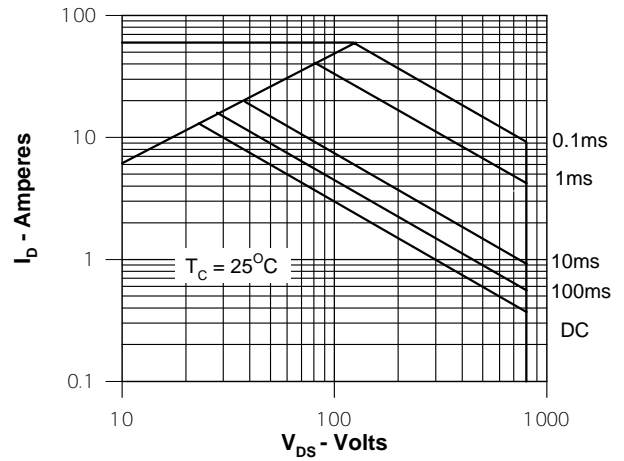


Figure 11. Transient Thermal Resistance

